

512K x 8 LOW VOLTAGE, ULTRA LOW POWER CMOS STATIC RAM

JANUARY 2008

FEATURES

- High-speed access time: 55ns, 70ns
- CMOS low power operation
 36 mW (typical) operating
 9 µW (typical) CMOS standby
- TTL compatible interface levels
- Single power supply
 1.65V 2.2V VDD (IS62WV5128ALL)
 2.5V 3.6V VDD (IS62WV5128BLL)
- Fully static operation: no clock or refresh required
- · Three state outputs
- Industrial temperature available
- Lead-free available

DESCRIPTION

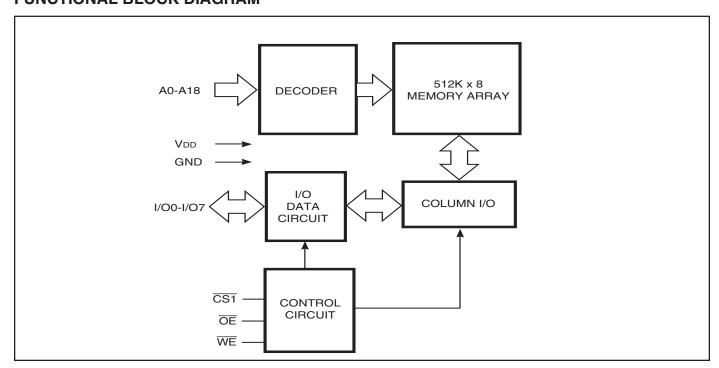
The *ISSI* IS62WV5128ALL / IS62WV5128BLL are high-speed, 4M bit static RAMs organized as 512K words by 8 bits. It is fabricated using *ISSI*'s high-performance CMOS technology. This highly reliable process coupled with innovative circuit design techniques, yields high-performance and low power consumption devices.

When $\overline{\text{CS1}}$ is HIGH (deselected) the device assumes a standby mode at which the power dissipation can be reduced down with CMOS input levels.

Easy memory expansion is provided by using Chip Enable and Output Enable inputs. The active LOW Write Enable (WE) controls both writing and reading of the memory.

The IS62WV5128ALL and IS62WV5128BLL are packaged in the JEDEC standard 32-pin TSOP (TYPE I), 32-pin sTSOP (TYPE I), 32-pin TSOP (Type II), 32-pin SOP and 36-pin mini BGA.

FUNCTIONAL BLOCK DIAGRAM

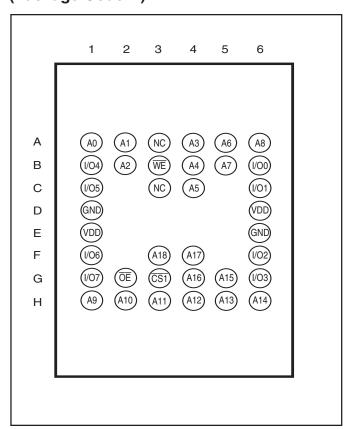




PIN DESCRIPTIONS

A0-A18	Address Inputs
CS1	Chip Enable 1 Input
ŌĒ	Output Enable Input
WE	Write Enable Input
I/O0-I/O7	Input/Output
NC	No Connection
VDD	Power
GND	Ground

36-pin mini BGA (B) (6mm x 8mm) (Package Code B)



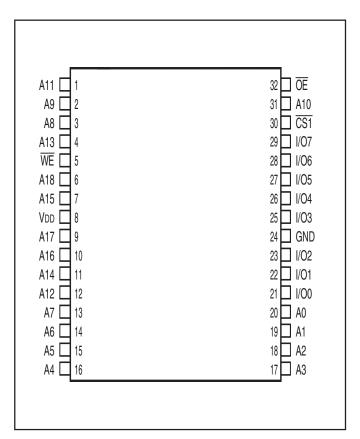


PIN DESCRIPTIONS

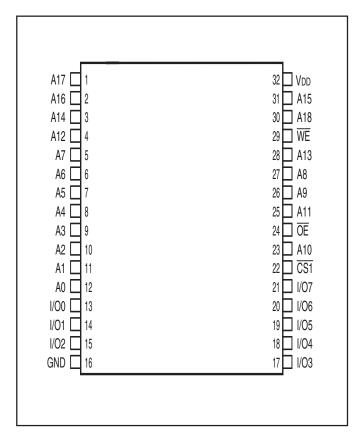
A0-A18	Address Inputs
CS1	Chip Enable 1 Input
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I/O0-I/O7	Input/Output
VDD	Power
GND	Ground

PIN CONFIGURATION

32-pin TSOP (TYPE I), (Package Code T) 32-pin sTSOP (TYPE I) (Package Code H)



32-pin SOP (Package Code Q) 32-pin TSOP (TYPE II) (Package Code T2)





OPERATING RANGE (VDD)

Range	Ambient Temperature	IS62WV5128ALL	IS62WV5128BLL
Commercial	0°C to +70°C	1.65V - 2.2V	2.5V - 3.6V
Industrial	-40°C to +85°C	1.65V - 2.2V	2.5V - 3.6V

ABSOLUTE MAXIMUM RATINGS(1)

Symbol	Parameter	Value	Unit	
VTERM	Terminal Voltage with Respect to GND	-0.2 to VDD+0.3	V	
VDD	VDD Related to GND	-0.2 to VDD+0.3	V	
Тѕтс	Storage Temperature	-65 to +150	°C	
Рт	Power Dissipation	1.0	W	

Note:

DC ELECTRICAL CHARACTERISTICS (Over Operating Range)

Symbol	Parameter	Test Conditions	V _{DD}	Min.	Max.	Unit
Vон	Output HIGH Voltage	Iон = -0.1 mA	1.65-2.2V	1.4	_	V
		IOH = -1 mA	2.5-3.6V	2.2	_	V
Vol	Output LOW Voltage	IoL = 0.1 mA	1.65-2.2V	_	0.2	V
		IoL = 2.1 mA	2.5-3.6V	_	0.4	V
VIH	Input HIGH Voltage		1.65-2.2V	1.4	V _{DD} + 0.2	V
			2.5-3.6V	2.2	$V_{DD} + 0.3$	V
VIL ⁽¹⁾	Input LOW Voltage		1.65-2.2V	-0.2	0.4	V
			2.5-3.6V	-0.2	0.6	V
ILI	Input Leakage	$GND \leq V_{IN} \leq V_{DD}$		-1	1	μΑ
ILO	Output Leakage	GND≤Vout≤Vdd, Ou	utputs Disabled	– 1	1	μΑ

Notes:

Stress greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is
a stress rating only and functional operation of the device at these or any other conditions above those indicated in the
operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods
may affect reliability.

^{1.} V_{IL} (min.) = -1.0V for pulse width less than 10 ns.



CAPACITANCE(1)

Symbol	Parameter	Conditions	Max.	Unit
CIN	Input Capacitance	VIN = 0V	8	pF
Соит	Input/Output Capacitance	Vout = 0V	10	pF

Note:

AC TEST CONDITIONS

Parameter	IS62WV5128ALL (Unit)	IS62WV5128BLL (Unit)	
Input Pulse Level	0.4V to VDD-0.2V	0.4V to V _{DD} -0.3V	
Input Rise and Fall Times	5 ns	5ns	
Input and Output Timing and Reference Level	VREF	VREF	
Output Load	See Figures 1 and 2	See Figures 1 and 2	

	IS62WV5128ALL 1.65 - 2.2V	IS62WV5128BLL 2.5V - 3.6V
R1(Ω)	3070	3070
R2(Ω)	3150	3150
VREF	0.9V	1.5V
Vтм	1.8V	2.8V

AC TEST LOADS

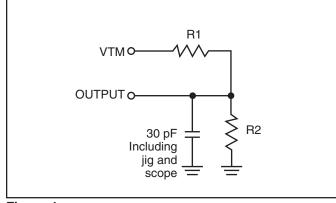


Figure 1

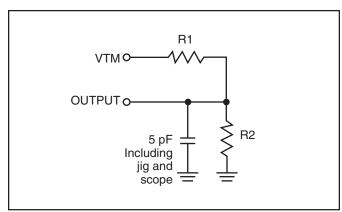


Figure 2

^{1.} Tested initially and after any design or process changes that may affect these parameters.



POWER SUPPLY CHARACTERISTICS⁽¹⁾ (Over Operating Range)

62WV5128ALL (1.65V-2.2V)

Symbol	Parameter	Test Conditions		Max. 70 ns	Unit
lcc	VDD Dynamic Operating Supply Current	VDD=Max., IOUT=0mA,f=fmax	Com. Ind.	25 30	mA
lcc1	Operating Supply Current	VDD=Max., CS1 =0.2\ WE =VDD-0.2V f=1MHZ	/ Com. Ind.	10 10	mA
ISB1	TTL Standby Current (TTL Inputs)	VDD=Max., VIN=VIHORVIL CS1=VIH, f=1MHz	Com. Ind.	0.35 0.35	mA
ISB2	CMOS Standby Current (CMOS Inputs)	V _{DD} =Max., CS1 ≥V _{DD} -0.2V, V _{IN} ≥V _{DD} -0.2V, or V _{IN} ≤0.2V, f=0	Com. Ind.	15 15	μΑ

Note

POWER SUPPLY CHARACTERISTICS⁽¹⁾ (Over Operating Range)

62WV5128BLL (2.5V-3.6V)

Symbol	Parameter	Test Conditions		Max. 55 ns	Unit
lcc	VDD Dynamic Operating Supply Current	VDD = Max., IOUT = 0 mA, f = fmax	Com. Ind.	40 45	mA
Icc1	Operating Supply Current	$V_{DD} = Max., \overline{CS1} = 0.2V$ $\overline{WE} = V_{DD}-0.2V$ $f=1_{MHZ}$	Com. Ind.	15 15	mA
ISB1	TTL Standby Current (TTL Inputs)	VDD = Max., VIN = VIH OR VIL CS1 = VIH, f = 1 MHz	Com. Ind.	0.35 0.35	mA
IsB2	CMOS Standby Current (CMOS Inputs)	$\begin{aligned} & \frac{\text{VDD}}{\text{CS1}} \geq \text{Max.}, \\ & \overline{\text{CS1}} \geq \text{VDD} - 0.2\text{V}, \\ & \text{VIN} \geq \text{VDD} - 0.2\text{V}, \text{ or} \\ & \text{VIN} \leq 0.2\text{V}, \text{ f} = 0 \end{aligned}$	Com. Ind.	15 15	μΑ

Note:

^{1.} At f = fmax, address and data inputs are cycling at the maximum frequency, f = 0 means no input lines change.

^{1.} At f = fmax, address and data inputs are cycling at the maximum frequency, f = 0 means no input lines change.



READ CYCLE SWITCHING CHARACTERISTICS⁽¹⁾ (Over Operating Range)

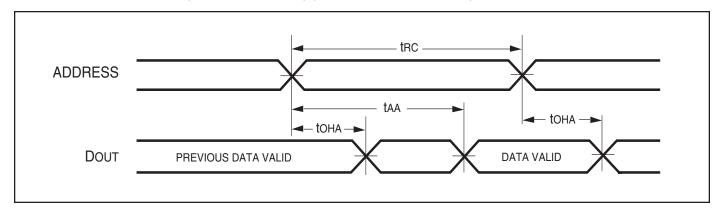
		55 ו	ns	70 ns	3	
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
trc	Read Cycle Time	55	_	70	_	ns
taa	Address Access Time	_	55	_	70	ns
t oha	Output Hold Time	10	_	10	_	ns
t _{ACS1}	CS1 Access Time	_	55	_	70	ns
tdoe	OE Access Time	_	25	_	35	ns
thzoe(2)	OE to High-Z Output	_	20	_	25	ns
tLZOE ⁽²⁾	OE to Low-Z Output	5	_	5	_	ns
thzcs1	CS1 to High-Z Output	0	20	0	25	ns
tLZCS1	CS1 to Low-Z Output	10	_	10	_	ns

Notes:

- 1. Test conditions assume signal transition times of 5 ns or less, timing reference levels of 0.9V/1.5V, input pulse levels of 0.4 to VDD-0.2V/VDD-0.3V and output loading specified in Figure 1.
- 2. Tested with the load in Figure 2. Transition is measured ±500 mV from steady-state voltage. Not 100% tested.

AC WAVEFORMS

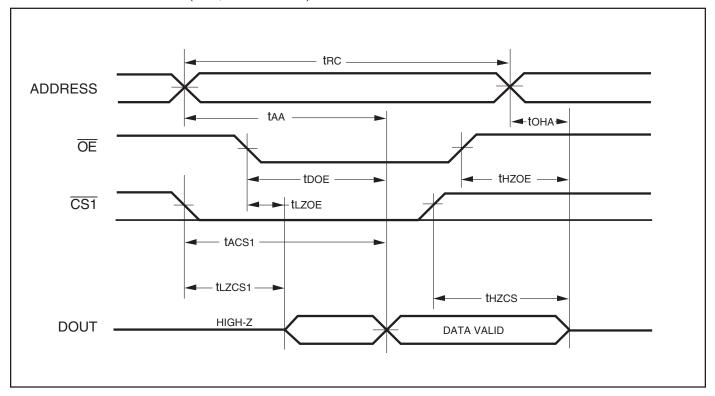
READ CYCLE NO. $1^{(1,2)}$ (Address Controlled) ($\overline{CS1} = \overline{OE} = VIL, \overline{WE} = VIH)$





AC WAVEFORMS

READ CYCLE NO. 2^(1,3) (CS1, OE Controlled)



Notes:

- 1. WE is HIGH for a Read Cycle.
- 2. The device is continuously selected. $\overline{\text{OE}}$, $\overline{\text{CS1}}=\text{V}_{\text{IL}}$. $\overline{\text{WE}}=\text{V}_{\text{IH}}$.
- 3. Address is valid prior to or coincident with CS1 LOW transition.



WRITE CYCLE SWITCHING CHARACTERISTICS(1,2) (Over Operating Range)

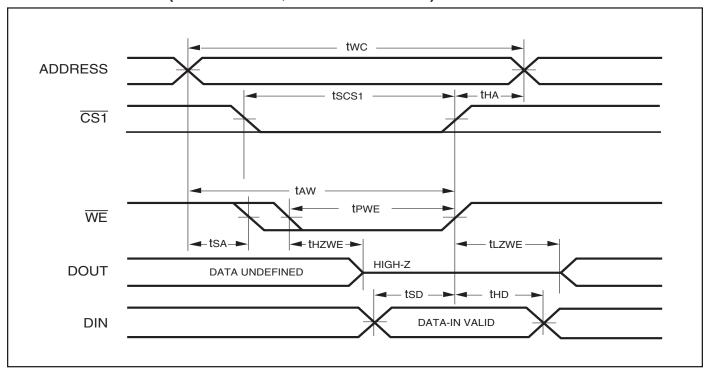
			ns	70	ns	
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
twc	Write Cycle Time	55	_	70	_	ns
tscs1	CS1 to Write End	45	_	60	_	ns
taw	Address Setup Time to Write End	45	_	60	_	ns
tна	Address Hold from Write End	0	_	0	_	ns
tsa	Address Setup Time	0	_	0	_	ns
t PWE	WE Pulse Width	40	_	50	_	ns
tsp	Data Setup to Write End	25	_	30	_	ns
t HD	Data Hold from Write End	0	_	0	_	ns
thzwe ⁽³⁾	WE LOW to High-Z Output	_	20	_	20	ns
tlzwe ⁽³⁾	WE HIGH to Low-Z Output	5	_	5	_	ns

Notes:

- 1. Test conditions assume signal transition times of 5 ns or less, timing reference levels of 0.9V/1.5V, input pulse levels of 0.4V to VDD-0.2V/VDD-0.3V and output loading specified in Figure 1.
- 2. The internal write time is defined by the overlap of CS1 LOW and WE LOW. All signals must be in valid states to initiate a Write, but any one can go inactive to terminate the Write. The Data Input Setup and Hold timing are referenced to the rising or falling edge of the signal that terminates the write.
- 3. Tested with the load in Figure 2. Transition is measured ±500 mV from steady-state voltage. Not 100% tested.

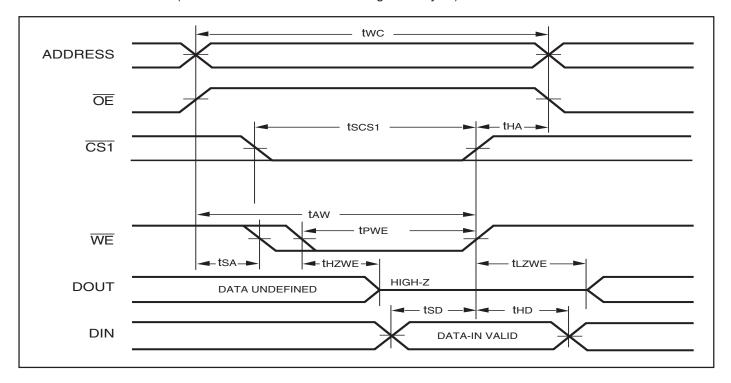
AC WAVEFORMS

WRITE CYCLE NO. 1 (CS1 Controlled, OE = HIGH or LOW)

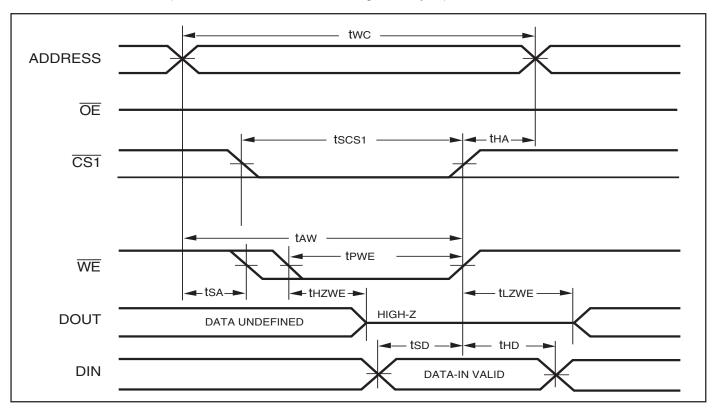




WRITE CYCLE NO. 2 (WE Controlled: OE is HIGH During Write Cycle)



WRITE CYCLE NO. 3 ($\overline{\text{WE}}$ Controlled: $\overline{\text{OE}}$ is LOW During Write Cycle)

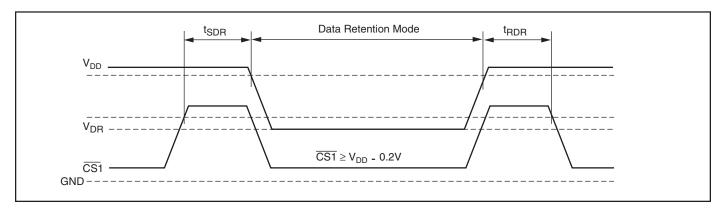




DATA RETENTION SWITCHING CHARACTERISTICS

Symbol	Parameter	Test Condition	Min.	Max.	Unit
VDR	VDD for Data Retention	See Data Retention Waveform	1.2	3.6	V
IDR	Data Retention Current	$V_{DD} = 1.2V, \overline{CS1} \ge V_{DD} - 0.2V$	_	15	μΑ
tsdr	Data Retention Setup Time	See Data Retention Waveform	0	_	ns
trdr	Recovery Time	See Data Retention Waveform	trc	_	ns

DATA RETENTION WAVEFORM (CS1 Controlled)



01/29/08



ORDERING INFORMATION IS62WV5128ALL (1.65V-2.2V)

Industrial Range: -40°C to +85°C

Speed (ns)	Order Part No.	Package
70	IS62WV5128ALL-70TI	TSOP, TYPE I
70	IS62WV5128ALL-70T2I	TSOP, TYPE II
70	IS62WV5128ALL-70HI	sTSOP, TYPE I
70	IS62WV5128ALL-70BI	mini BGA (6mmx8mm)

ORDERING INFORMATION

IS62WV5128BLL (2.5V - 3.6V)

Commercial Range: 0°C to +70°C

Speed (ns)	Order Part No.	Package
55	IS62WV5128BLL-55H	sTSOP, TYPE I

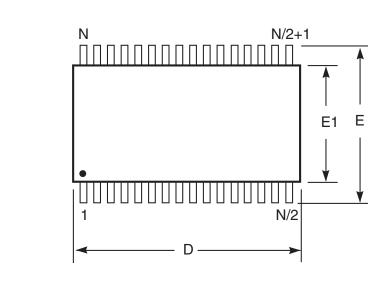
Industrial Range: -40°C to +85°C

Speed (ns)	Order Part No.	Package
55	IS62WV5128BLL-55TI	TSOP, TYPE I
55	IS62WV5128BLL-55TLI	TSOP, TYPE I, Lead-free
55	IS62WV5128BLL-55QLI	SOP, Lead-free
55	IS62WV5128BLL-55T2I	TSOP, TYPE II
55	IS62WV5128BLL-55T2LI	TSOP, TYPE II, Lead-free
55	IS62WV5128BLL-55HI	sTSOP, TYPE I
55	IS62WV5128BLL-55HLI	sTSOP, TYPE I, Lead-free
55	IS62WV5128BLL-55BI	mini BGA (6mmx8mm)
55	IS62WV5128BLL-55BLI	mini BGA (6mmx8mm), Lead-free



Plastic TSOP

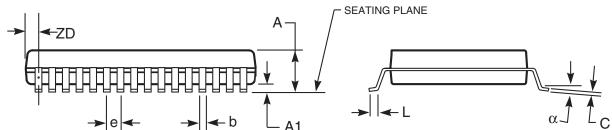
Package Code: T (Type II)



Notes:

- 1. Controlling dimension: millimieters, unless otherwise specified.
- unless otherwise specified.

 BSC = Basic lead spacing between centers.
- Dimensions D and E1 do not include mold flash protrusions and should be measured from the bottom of the package.
- 4. Formed leads shall be planar with respect to one another within 0.004 inches at the seating plane.

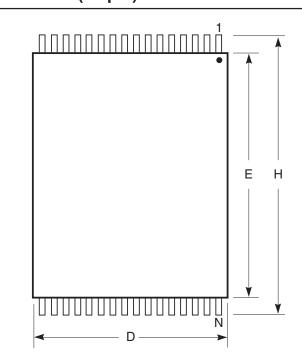


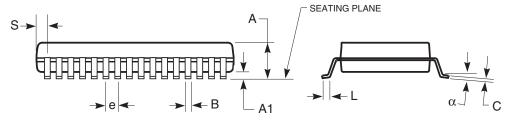
					Plastic T	SOP (T -	· Type II)					
	Millim	eters	Inche	S	Millim	eters	Inche	es	Millin	neters	Inch	es
Symbol	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max
Ref. Std.												
No. Leads	(N)	32	2			44	1				50	
Α	_	1.20	_	0.047	_	1.20	_	0.047	_	1.20	_	0.047
A1	0.05	0.15	0.002	0.006	0.05	0.15	0.002	0.006	0.05	0.15	0.002	0.006
b	0.30	0.52	0.012	0.020	0.30	0.45	0.012	0.018	0.30	0.45	0.012	0.018
С	0.12	0.21	0.005	0.008	0.12	0.21	0.005	0.008	0.12	0.21	0.005	0.008
D	20.82	21.08	0.820	0.830	18.31	18.52	0.721	0.729	20.82	21.08	0.820	0.830
E1	10.03	10.29	0.391	0.400	10.03	10.29	0.395	0.405	10.03	10.29	0.395	0.405
Е	11.56	11.96	0.451	0.466	11.56	11.96	0.455	0.471	11.56	11.96	0.455	0.471
е	1.27	BSC	0.050	BSC	0.80	BSC	0.032	BSC	0.80	BSC	0.031	BSC
L	0.40	0.60	0.016	0.024	0.41	0.60	0.016	0.024	0.40	0.60	0.016	0.024
ZD	0.95	REF	0.037	7 REF	0.81	REF	0.032	2 REF	0.88	REF	0.035	REF
α	0°	5°	0°	5°	0°	5°	0°	5°	0°	5°	0°	5°



Plastic TSOP-Type I

Package Code: T (32-pin)





	MILLIM	ETERS		INC	HES
Symbol	Min.	Max.		Min.	Max.
No. Leads			32		
Α	_	1.20		_	0.047
A1	0.05	0.25		0.002	0.010
В	0.17	0.23		0.007	0.009
С	0.12	0.17		0.005	0.007
D	7.90	8.10		0.311	0.319
Е	18.30	18.50		0.720	0.728
Н	19.80	20.20		0.780	0.795
е	0.50 l	0.50 BSC		0.020	BSC
L	0.40	0.60		0.016	0.024
α	0°	8°		0°	8°
S	0.25 l	REF		0.010	REF

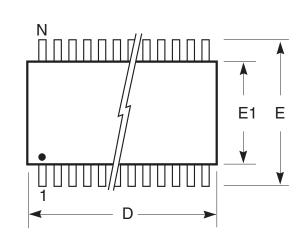
Notes:

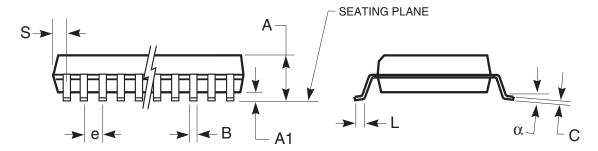
- 1. Controlling dimension: millimeters, unless otherwise specified.
- 2. BSC = Basic lead spacing between centers.
- Dimensions D and E do not include mold flash protrusions and should be measured from the bottom of the package.
- Formed leads shall be planar with respect to one another within 0.004 inches at the seating plane.



450-mil Plastic SOP

Package Code: Q (32-pin)





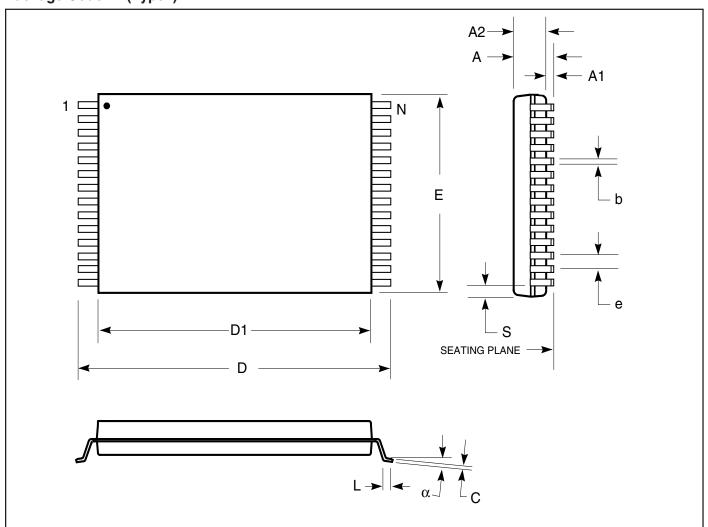
	MILLIM	ETERS		INC	HES
Symbol	Min.	Max.		Min.	Max.
No. Leads			32		
A	_	3.00		_	0.118
A1	0.10	_		0.004	_
В	0.36	0.51		0.014	0.020
С	0.15	0.30		0.006	0.012
D	20.14	20.75		0.793	0.817
Е	13.87	14.38		0.546	0.566
E1	11.18	11.43		0.440	0.450
е	1.27	BSC		0.050	BSC
L	0.58	0.99		0.023	0.039
α	0°	10°		0°	10°
S	_	0.86		_	0.034

Notes:

- 1. Controlling dimension: inches, unless otherwise specified.
- 2. BSC = Basic lead spacing between centers.
- 3. Dimensions D and E1 do not include mold flash protrusions and should be measured from the bottom of the package.
- Formed leads shall be planar with respect to one another within 0.004 inches at the seating plane.



Plastic STSOP - 32 pins Package Code: H (Type I)



Plastic STSOP (H - Type I)						
	Millim	eters	Inches			
Symbol	Min	Max	M	in	Max	
Ref. Std.						
N			32			
Α	_	1.25	_	-	0.049	
A1	0.05	_	0.0	02	_	
A2	0.95	1.05	0.0	37	0.041	
b	0.17	0.23	0.0	07	0.009	
С	0.14	0.16	0.00	055	0.0063	
D	13.20	13.60	0.5	20	0.535	
D1	11.70	11.90	0.4	61	0.469	
Е	7.90	8.10	0.3	11	0.319	
е	0.50	BSC	(0.020	BSC	
L	0.30	0.70	0.0	12	0.028	
S	0.28	Тур.	(0.011	I Тур.	
α	0°	5°	0	0	5°	

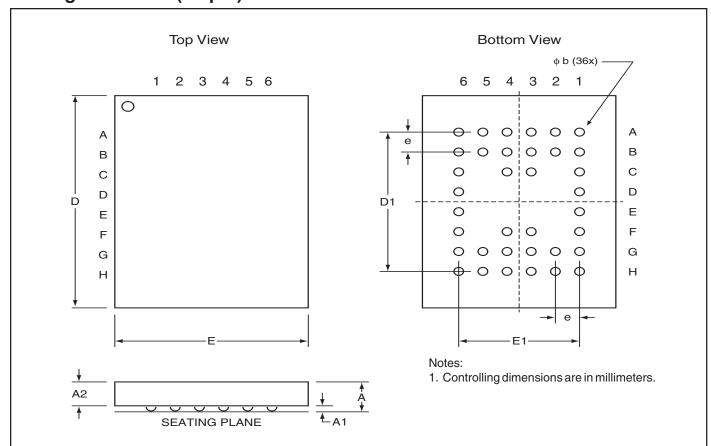
Notes:

- Controlling dimension: millimeters, unless otherwise specified.
- 2. BSC = Basic lead spacing between centers.
- Dimensions D1 and E do not include mold flash protrusions and should be measured from the bottom of the package.
- Formed leads shall be planar with respect to one another within 0.004 inches at the seating plane.



Mini Ball Grid Array

Package Code: B (36-pin)



mBGA - 6mm x 8mm

	MILLIMETERS			INCHES
Sym.	Min.	Тур.	Max.	Min. Typ. Max.
N0. Leads		36		36
Α	_	_	1.20	— — 0.047
A1	0.24	_	0.30	0.009 — 0.012
A2	0.60	_	_	0.024 — —
D	7.90	8.00	8.10	0.311 0.315 0.319
D1	5	.25BS	3	0.207BSC
E	5.90	6.00	6.10	0.232 0.236 0.240
E1	3.75BSC			0.148BSC
е	0	.75BS	C	0.030BSC
b	0.30	0.35	0.40	0.012 0.014 0.016

mBGA - 8mm x 10mm

	MIL	LIMET	ER	INCHES
Sym.	Min.	Тур.	Max.	Min. Typ. Max.
N0. Leads		36		36
Α	_	_	1.20	— — 0.047
A1	0.24	_	0.30	0.009 — 0.012
A2	0.60	_	_	0.024 — —
D	9.90	10.00	10.10	0.390 0.394 0.398
D1	5	.25BSC)	.207BSC
E	7.90	8.00	8.10	0.311 0.315 0.319
E1	3	3.75BSC)	0.148BSC
е	0	.75BSC)	0.030BSC
b	0.30	0.35	0.40	0.012 0.014 0.016

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